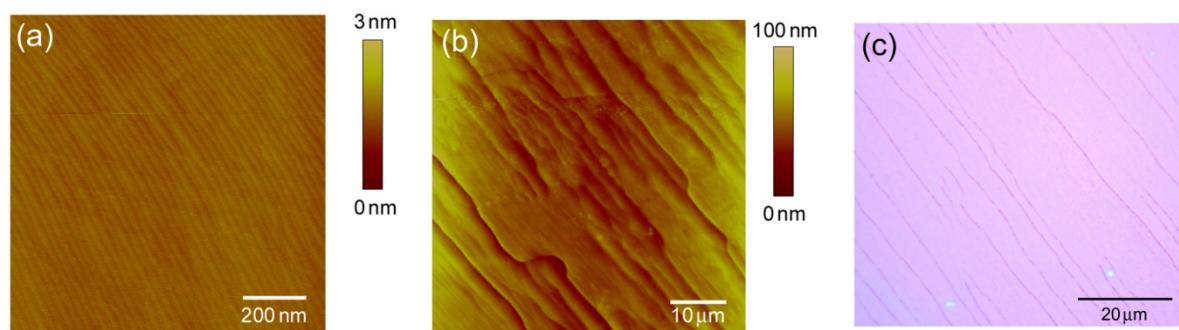


## Supplemental Information

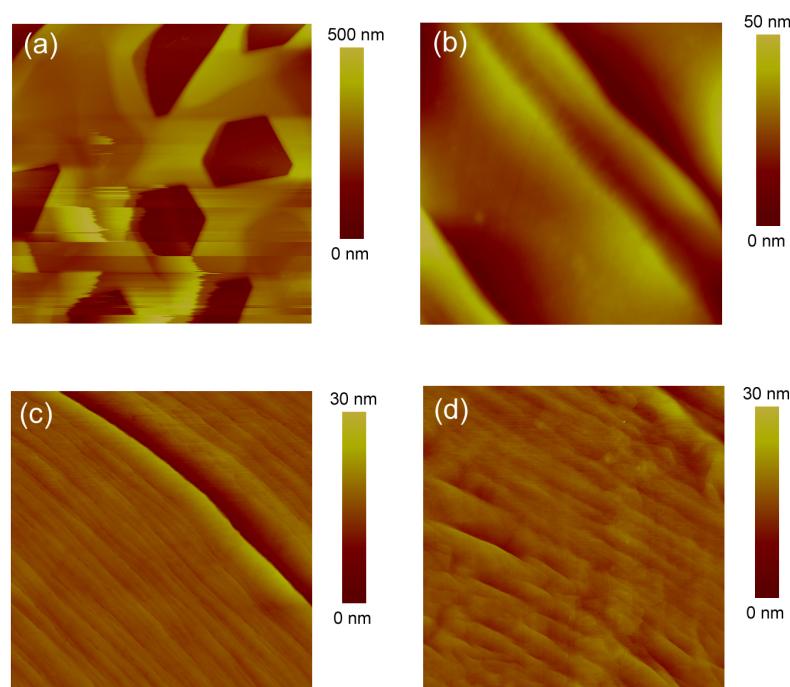
### Step-templated CVD growth of aligned graphene nanoribbons supported by single-layer graphene film

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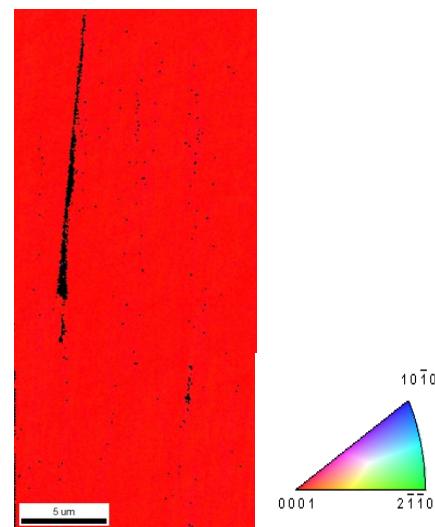
Institute for Materials Chemistry and Engineering and Graduate School of Engineering Sciences, Kyushu University, Kasuga, Fukuoka 816-8580, Japan



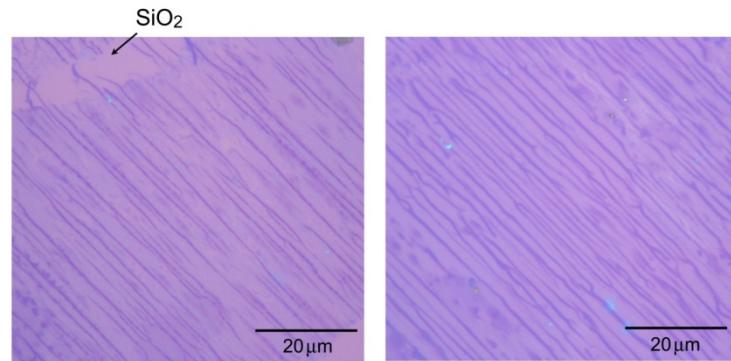
**Figure S1.** (a) AFM image of the sapphire surface with low miscut angle ( $0.8^\circ$ ). The sapphire was annealed in air at  $900\text{ }^\circ\text{C}$  before the measurement. (b) AFM image of Co surface measured after CVD. (c) Optical micrograph of transferred graphene film on a SiO<sub>2</sub>/Si substrate.



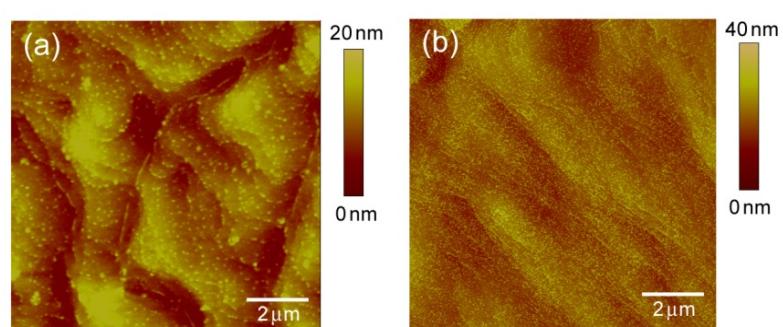
**Figure S2.** AFM images of the surface of Co film after CVD with different pre-annealing conditions (the sapphire with miscut angle 2.0° was used as a substrate). The graphene growth was carried out by flowing CH<sub>4</sub>/H<sub>2</sub>/Ar mixed gas at 1000 °C for 20 min. (a) No H<sub>2</sub> pre-treatment prior to the graphene growth at 1000 °C. (b) H<sub>2</sub> pre-annealing at 500 °C. (c,d) H<sub>2</sub> pre-annealing at 500 °C, followed by the second annealing at 1000 °C for 10 min (c) or 20 min (d). These images show the importance of H<sub>2</sub> pre-annealing processes at 500 and 1000 °C to induce the clear step/terrace structure on the Co surface. The longer annealing time at 1000 °C slightly deteriorates the step structure (d).



**Figure S3.** Crystallographic orientation of the Co film formed on miscut sapphire by electron backscatter diffraction (EBSD). The red contrast shows that the Co has (0001) plane normal to the substrate surface.



**Figure S4.** Optical microscope images of the transferred graphene film which was grown on the Co/sapphire (miscut angle is 2.0°). In the CVD, the cooling process was carried out in Ar/H<sub>2</sub> gas (96:4). The samples shown in Fig. 3 were cooled in pure H<sub>2</sub> flow, giving more uniform graphene sheet.



**Figure S5.** AFM image of the surface of Cu/sapphire substrate after CVD. The CVD temperature is 1000 °C (a) and 900 °C (b), and the sapphire with miscut angle of 2.0° is used.